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Murakami, Y., N. Kuratani, S. Nishiyama, O. Imai and K. Ogata, Study on the effect of the interlayer on the adhesion of 400 μm thick film . . . 121 (1997) 212

Nagasaka, H., A. Chayahara and K. Fujii, Tribological properties of titanium nitride films prepared by dynamic ion beam mixing method . . . 121 (1997) 279
Nagasawa, H., see Mameno, K. . . . 121 (1997) 311
Nakagawa, S.T., L. Thomé, H. Saito and C. Clerc, The 3-D profiling of B ions implanted into Si . . . 121 (1997) 36
Nakai, H., J. Shinohara, T. Sassa and Y. Ikegami, Surface morphology and resistivity of aluminum oxide films prepared by plasma CVD combined with ion beam irradiation . . . 121 (1997) 125
Nakamura, N., see Hanabusa, M. . . . 121 (1997) 367
Nakamura, T., see Kamijo, E. . . . 121 (1997) 110
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Nakashima, K., see Eryu, O. . . . 121 (1997) 419
Nakata, J., H. Yamazaki, Y. Yamamoto and Y. Kido, In-situ ion-beam annealing of damage in GaAs during O implantation and O-site determination by $^{18}O(p,\alpha)^{15}N$ nuclear reaction . . . 121 (1997) 306
Nakata, R., see Tanaka, K. . . . 121 (1997) 404
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Nomura, T., see Irie, M. . . . 121 (1997) 133
Nomura, T., see Oda, K. . . . 121 (1997) 283
Nonogaki, R., S. Yamada and T. Wada, Preparation of boron nitride films by multi-source plasma CVD method . . . 121 (1997) 121
Nozaki, S., S. Sato, H. Ono, H. Morisaki and M. Iwase, Germanium nanostructures deposited by the cluster-beam evaporation technique . . . 121 (1997) 455

Obata, T., see Gaze, J. . . . 121 (1997) 427
Obata, M., see Sano, Y. . . . 121 (1997) 432
Oda, K., A. Nakayama, H. Ohara, N. Kitagawa and T. Nomura, Characterization of ion implanted TiN films . . . 121 (1997) 283
Oda, K., see Yokota, K. . . . 121 (1997) 295

Odaka, H., see Haynes, T.E. . . . . 121 (1997) 221
Ogasawara, S., see Akizuki, M. . . . . 121 (1997) 166
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Ogawa, S., see Okamoto, A. . . . . 121 (1997) 179
Ogawa, S., M. Yoshitake, Y. Suzuki, K. Nishigaki, T. Sugioka and H. Toda, The effect of B and P ion implantation on superconducting magnetic shielding in NbTi sheets . . . . . 121 (1997) 328
Ogi, K., see Itsuki, A. . . . . 121 (1997) 116
Ogura, M., N. Yamaji, M. Imai, A. Itoh and N. Imanishi, Trapping of hydrogen in silicon-implanted aluminum . . . . 121 (1997) 470
Ohara, H., see Irie, M. . . . . 121 (1997) 133
Ohara, H., see Oda, K. . . . . 121 (1997) 283
Ohashi, K., see Ohashi, T. . . . . 121 (1997) 40
Ohashi, K., see Miyake, K. . . . . 121 (1997) 102
Ohashi, T., K. Miyake and K. Ohashi, Molecular dynamics simulations of low energy atomic collisions between an atom and a substrate: Effect of incident angle and energy . . . . . 121 (1997) 40
Ohdaira, T., see Hirata, K. . . . . 121 (1997) 267
Ohno, N., see Current, M.I. . . . . 121 (1997) 262
Ohno, N., see Taniguchi, J. . . . . 121 (1997) 507
Ohtani, S., M. Inoue and T. Takagi, Nitrogen distribution and microstructure of hot implanted Fe–Ti alloy films . . . 121 (1997) 319
Okada, F., see Tokita, K. . . . . 121 (1997) 408
Okamoto, A., see Suzuki, Y. . . . . 121 (1997) 107
Okamoto, A., Y. Suzuki, M. Yoshitake, S. Ogawa and N. Nakano, Gold–carbon composite thin films for electrochemical gas sensor prepared by reactive plasma sputtering . . . . . 121 (1997) 179
Okazaki, K., see Sano, Y. . . . . 121 (1997) 432
Ono, H., see Nozaki, S. . . . . 121 (1997) 455
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Paul, A., see Moro, L. . . . . 121 (1997) 151
Petravic, M., see Williams, J.S. . . . . 121 (1997) 24
Pindoria, G., F. Wang, M. Badaye and T. Morishita, Observation of long range disorder caused by low energy (20–200 eV) $O^+$ and $Ar^+$ beams, in NdBaCuO films . . . . . 121 (1997) 141
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Rehn, L.E., see Rüders, F. . . . . 121 (1997) 30
Rimini, E., A. La Ferla, G. Galvagno, S. Coffa, G. Franzò and F. Priolo, Oxygen-impurity interactions in crystalline silicon: The cases of aluminum and erbium . . . . . 121 (1997) 18
Rüders, F., L.E. Rehn, P.M. Baldo, E.E. Fullerton and S.D. Bader, Temperature-dependent study of ion-channeling in Fe/Cr superlattices . . . . . 121 (1997) 30
Ruoff, R.S., see Moro, L. . . . . 121 (1997) 151

Sadoh, T., see Baba, A. . . . . 121 (1997) 299
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Saito, H., see Nakagawa, S.T. . . . . 121 (1997) 36
Saito, K. and Y. Koga, Characterization of carbon films produced by laser ablation of graphite in helium and nitrogen gas atmosphere . . . . . 121 (1997) 400
Saito, K., see Itadani, T. . . . . 121 (1997) 415
Saitoh, K., S. Nakao, H. Niwa, M. Takeda and S. Miyagawa, On the possibility of channeled ion assisted epitaxial growth . . . . . 121 (1997) 84
Saitoh, K., see Miyagawa, Y. . . . . 121 (1997) 340
Saitoh, K., see Shimizu-Iwayama, T. . . . . 121 (1997) 450
Sano, Y., N. Mukai, K. Okazaki and M. Obata, Residual stress improvement in metal surface by underwater laser irradiation . . . . . 121 (1997) 432
Sassa, T., see Nakai, H. . . . . 121 (1997) 125

Sato, S., see Nozaki, S. . . . 121 (1997) 455
Satou, M., see Itsuki, A. . . . 121 (1997) 116
Seki, T., T. Kaneko, D. Takeuchi, T. Aoki, J. Matsuo, Z. Insepov and I. Yamada, STM observation of HOPG surfaces irradiated with Ar cluster ions . . . 121 (1997) 498
Setsuhara, Y., see Ebe, A. . . . 121 (1997) 207
Shibata, H., see Katsumata, H. . . . 121 (1997) 146
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Shimizu-Iwayama, T., S. Nakao and K. Saitoh, Optical and structural characterization of implanted nanocrystalline semiconductors . . . 121 (1997) 450
Shin, I., see Akizuki, M. . . . 121 (1997) 166
Shindo, T., see Iida, S. . . . 121 (1997) 162
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Shirai, N., see Tanaka, K. . . . 121 (1997) 404
Short, K.T., see Williams, J.S. . . . 121 (1997) 24
Singh, R.K. and J.M. Fitz-Gerald, Laser induced formation of micro-rough structures . . . 121 (1997) 363
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Suda, T., see Kakishita, K. . . . 121 (1997) 175
Suda, Y., T. Nakazono, K. Ebihara and K. Baba, Pulsed laser deposition of tungsten carbide thin films on silicon (100) substrate . . . 121 (1997) 396
Suehara, S., see Hishita, S. . . . 121 (1997) 157
Suehara, S., see Oyoshi, K. . . . 121 (1997) 184
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Suga, T., see Chung, T.R. . . . 121 (1997) 203
Suga, T., see Yang, L. . . . 121 (1997) 519
Sugihara, T. and K. Kuba, Selection of kinetic energy of laser-ablated particles and its application for deposition of Au, Pt and Ag thin films . . . 121 (1997) 392
Sugioka, T., see Ogawa, S. . . . 121 (1997) 328
Sugiyama, I., see Tanaka, K. . . . 121 (1997) 404
Suzuki, R., see Hirata, K. . . . 121 (1997) 267
Suzuki, Y., see Inoue, M. . . . 121 (1997) 1
Suzuki, Y., A. Okamoto, M. Yoshitake and S. Ogawa, Pt thin films prepared by low energy plasma sputtering . . . 121 (1997) 107
Suzuki, Y., see Okamoto, A. . . . 121 (1997) 179
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Taga, N., see Haynes, T.E. . . . 121 (1997) 221
Tahara, H., T. Kawabata, L. Zhang, T. Yasui and T. Yoshikawa, Exposure of spacecraft polymers to energetic ions, electrons and ultraviolet light . . . 121 (1997) 446
Takagi, T., see Inoue, M. . . . 121 (1997) 1
Takagi, T., see Ohtani, S. . . . 121 (1997) 319
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Takaoka, G.H., see Kawashita, M. . . . 121 (1997) 323
Takaoka, G.H., see Tanomura, M. . . . 121 (1997) 480
Takaoka, G.H., T. Hamano, K. Fukushima, J. Matsuo and I. Yamada, Preparation and catalytic activity of nano-scale Au islands supported on $TiO_2$ . . . 121 (1997) 503
Takase, M. and B. Mizuno, An evaluation method for a high concentration profile produced in very low energy doping processes . . . 121 (1997) 288
Takeda, M., see Saitoh, K. . . . 121 (1997) 84
Takeshita, H., see Mitamura, T. . . . 121 (1997) 271
Takeuchi, D., N. Shimada, J. Matsuo and I. Yamada, Shallow junction formation by polyatomic cluster ion implantation . . . 121 (1997) 345
Takeuchi, D., K. Fukushima, J. Matsuo and I. Yamada, Study of Ar cluster ion bombardment of a sapphire surface . . . 121 (1997) 493

Takeuchi, D., see Tanomura, M. . . . . 121 (1997) 480
Takeuchi, D., see Seki, T. . . . . 121 (1997) 498
Takeuchi, T., see Kiuchi, M. . . . . 121 (1997) 154
Tanaka, K., N. Shirai, I. Sugiyama and R. Nakata, Pulsed laser deposition of $CdWO_4$ . . . . . 121 (1997) 404
Tanaka, T., see Ikeyama, M. . . . . 121 (1997) 335
Tanaka, Y., see Yamada, T. . . . . 121 (1997) 378
Tani, Y., see Kamijo, E. . . . . 121 (1997) 110
Taniguchi, J., I. Miyamoto, N. Ohno and S. Honda, Utilizing of hydrocarbon contamination for prevention of the surface charge-up at electron-beam assisted chemical etching of a diamond chip . . . . . 121 (1997) 507
Tanimura, S., see Fuchigami, H. . . . . 121 (1997) 422
Tanomura, M., D. Takeuchi, J. Matsuo, G.H. Takaoka and I. Yamada, Fullerene ion irradiation to silicon . . . . . 121 (1997) 480
Terasawa, M., see Mitamura, T. . . . . 121 (1997) 271
Terasawa, M., see Fan, X. . . . . 121 (1997) 331
Terasawa, M., see Yamamoto, A. . . . . 121 (1997) 275
Thomé, L., see Nakagawa, S.T. . . . . 121 (1997) 36
Thomé, L. and F. Garrido, Formation of metallic nanophases in insulators by high-energy ion-beam mixing . . . . . 121 (1997) 237
Toda, H., see Ogawa, S. . . . . 121 (1997) 328
Tokita, K. and F. Okada, Fabrication of $PbTiO_3$ thin films by laser metalorganic chemical vapor deposition . . . . . 121 (1997) 408
Toyoda, N., see Matsuo, J. . . . . 121 (1997) 459
Toyoda, N., H. Kitani, J. Matsuo and I. Yamada, Reactive sputtering by $SF_6$ cluster ion beams . . . . . 121 (1997) 484
Toyoda, N., see Kitani, H. . . . . 121 (1997) 489
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Wielunski, L.S., see Ikeyama, M. . . . . 121 (1997) 335
Williams, J.S., K.T. Short, M. Petravic and B.G. Svensson, Oxidation of silicon by low energy oxygen ions . . . . . 121 (1997) 24
Wilson, M., see Horwitz, J.S. . . . . 121 (1997) 371
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Yamada, I., see Toyoda, N. . . . . 121 (1997) 484
Yamada, I., see Kitani, H. . . . . 121 (1997) 489
Yamada, I., see Takeuchi, D. . . . . 121 (1997) 493
Yamada, I., see Seki, T. . . . . 121 (1997) 498
Yamada, I., see Takaoka, G.H. . . . . 121 (1997) 503

Yamada, S., see Nonogaki, R. . . . . 121 (1997) 121
Yamada, T., Y. Tanaka, T. Suemasu and Y. Kohtoku, Synthesis and characterization of $SiC-Si_3N_4$ composites by dual irradiation of $CO_2$ and excimer lasers . . . . . 121 (1997) 378
Yamaji, N., see Ogura, M. . . . . 121 (1997) 470
Yamamoto, A., H. Tsubakino, M. Ando, M. Terasawa and T. Mitamura, Effects of ion-implantation with nitrogen ion on microstructures in deformed iron . . . . . 121 (1997) 275
Yamamoto, A., see Fan, X. . . . . 121 (1997) 331
Yamamoto, M., see Kiuchi, M. . . . . 121 (1997) 154
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Yamamuro, K., see Morita, E. . . . . 121 (1997) 412
Yamazaki, H., see Nakata, J. . . . . 121 (1997) 306
Yang, J.J. and L.J. Chen, High resolution transmission electron microscope study of solid phase epitaxial growth of very high dose, low energy $P^+$ implanted (001)Si . . . . . 121 (1997) 195
Yang, J.J. and L.J. Chen, Characterization and removal of residual defects in high dose, very low energy $BF_2^+$-implanted (001)Si . . . . . 121 (1997) 291
Yang, L., see Chung, T.R. . . . . 121 (1997) 203
Yang, L., N. Hosoda and T. Suga, TEM investigation of the stainless steel/aluminum interface created by the surface activated bonding method . . . . . 121 (1997) 519
Yasui, I., see Haynes, T.E. . . . . 121 (1997) 221
Yasui, T., see Tahara, H. . . . . 121 (1997) 446
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Yokota, K., K. Hosokawa, K. Oda, F. Miyashita, K. Hirai, H. Takano, M. Kumagai, Y. Ando and K. Matsuda, Reliability of shallow $n^+$-type layers formed in dual As and B implanted silicon by rapid thermal annealing . . . . 121 (1997) 295
Yoneda, T., see Kajiyama, K. . . . . 121 (1997) 315
Yoon, Y.H., see Lee, J.W. . . . . 121 (1997) 474
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